

# Harri Lipsanen

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

358  
papers

6,404  
citations

40  
h-index

64  
g-index

406  
ext. papers

7,349  
ext. citations

3.7  
avg, IF

5.67  
L-index

#	Paper	IF	Citations
358	Femtosecond Mode-locked Yb:KYW Laser Based on InP Nanowire Saturable Absorber. <i>IEEE Photonics Technology Letters</i> , <b>2022</b> , 1-1	2.2	0
357	InSb Nanowire Direct Growth on Plastic for Monolithic Flexible Device Fabrication. <i>ACS Applied Electronic Materials</i> , <b>2022</b> , 4, 539-545	4	1
356	WITio: A MATLAB data evaluation toolbox to script broader insights into big data from WITec microscopes. <i>SoftwareX</i> , <b>2022</b> , 18, 101009	2.7	1
355	Engineering the Dipole Orientation and Symmetry Breaking with Mixed-Dimensional Heterostructures.. <i>Advanced Science</i> , <b>2022</b> , e2200082	13.6	1
354	Probing Electronic States in Monolayer Semiconductors through Static and Transient Third-Harmonic Spectroscopies. <i>Advanced Materials</i> , <b>2021</b> , e2107104	24	0
353	Optical amplification by surface-plasmon-resonant Au grating substrates: Monolayer MoS2 with 170-fold second harmonic generation and 3-fold (off-resonance) Raman scattering. <i>Superlattices and Microstructures</i> , <b>2021</b> , 160, 107077	2.8	1
352	Multilayer MoTe2 Field-Effect Transistor at High Temperatures. <i>Advanced Materials Interfaces</i> , <b>2021</b> , 8, 2100950	4.6	2
351	Tuning of Emission Wavelength of CaS:Eu by Addition of Oxygen Using Atomic Layer Deposition. <i>Materials</i> , <b>2021</b> , 14,	3.5	2
350	Trends in Carbon, Oxygen, and Nitrogen Core in the X-ray Absorption Spectroscopy of Carbon Nanomaterials: A Guide for the Perplexed. <i>Journal of Physical Chemistry C</i> , <b>2021</b> , 125, 973-988	3.8	8
349	Deterministic Modification of CVD Grown Monolayer MoS2 with Optical Pulses. <i>Advanced Materials Interfaces</i> , <b>2021</b> , 8, 2002119	4.6	2
348	Symmetry Reduction in FEM Optics Modeling of Single and Periodic Nanostructures. <i>Symmetry</i> , <b>2021</b> , 13, 752	2.7	1
347	Applied electromagnetic optics simulations for nanophotonics. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 131102	2.5	4
346	Optical Modification of Monolayer MoS2: Deterministic Modification of CVD Grown Monolayer MoS2 with Optical Pulses (Adv. Mater. Interfaces 10/2021). <i>Advanced Materials Interfaces</i> , <b>2021</b> , 8, 2170056	4.6	5
345	All-parylene flexible wafer-scale graphene thin film transistor. <i>Applied Surface Science</i> , <b>2021</b> , 551, 149416	6.7	5
344	Effect of crystal structure on the Young's modulus of GaP nanowires. <i>Nanotechnology</i> , <b>2021</b> , 32,	3.4	1
343	GaAs surface passivation for InAs/GaAs quantum dot based nanophotonic devices. <i>Nanotechnology</i> , <b>2021</b> , 32, 130001	3.4	2
342	Giant All-Optical Modulation of Second-Harmonic Generation Mediated by Dark Excitons. <i>ACS Photonics</i> , <b>2021</b> , 8, 2320-2328	6.3	3

341	Ultrafast carrier dynamics and nonlinear optical response of InAsP nanowires. <i>Photonics Research</i> , <b>2021</b> , 9, 1811	6	2
340	Mechanical and optical properties of as-grown and thermally annealed titanium dioxide from titanium tetrachloride and water by atomic layer deposition. <i>Thin Solid Films</i> , <b>2021</b> , 732, 138758	2.2	7
339	Single-step chemical vapour deposition of anti-pyramid MoS/WS vertical heterostructures. <i>Nanoscale</i> , <b>2021</b> , 13, 4537-4542	7.7	8
338	Experimental Study and Simulation of the Spectral Characteristics of LED Heterostructures with an InAs Active Region. <i>Technical Physics Letters</i> , <b>2020</b> , 46, 150-153	0.7	2
337	Direct Growth of Light-Emitting III-V Nanowires on Flexible Plastic Substrates. <i>ACS Nano</i> , <b>2020</b> , 14, 7484-7491	7.9	14
336	Management of light and scattering in InP NWs by dielectric polymer shell. <i>Nanotechnology</i> , <b>2020</b> , 31, 384003	3.4	3
335	Metalorganic vapor phase epitaxy of wurtzite InP nanowires on GaN. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 093101	3.4	1
334	Geometry Tailoring of Emission from Semiconductor Nanowires and Nanocones. <i>Photonics</i> , <b>2020</b> , 7, 23	2.2	6
333	Production and processing of graphene and related materials. <i>2D Materials</i> , <b>2020</b> , 7, 022001	5.9	179
332	Photodegradation of surface passivated GaAs nanowires. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1461, 012002	0.3	
331	Erbium-doped hybrid waveguide amplifiers with net optical gain on a fully industrial 300 mm silicon nitride photonic platform. <i>Optics Express</i> , <b>2020</b> , 28, 27919-27926	3.3	13
330	Nonlinear optical absorption properties of InP nanowires and applications as a saturable absorber. <i>Photonics Research</i> , <b>2020</b> , 8, 1035	6	4
329	Nanowire-assisted microcavity in a photonic crystal waveguide and the enabled high-efficiency optical frequency conversions. <i>Photonics Research</i> , <b>2020</b> , 8, 1734	6	1
328	Comparison of absorption simulation in semiconductor nanowire and nanocone arrays with the Fourier modal method, the finite element method, and the finite-difference time-domain method. <i>Nano Express</i> , <b>2020</b> , 1, 030034	2	6
327	Tailoring the longitudinal electric fields of high-order laser beams and their direct verification in three dimensions. <i>Optics Communications</i> , <b>2020</b> , 459, 124894	2	1
326	High performance complementary WS devices with hybrid Gr/Ni contacts. <i>Nanoscale</i> , <b>2020</b> , 12, 21280-21290	7.9	8
325	Superhydrophobic Antireflection Coating on Glass Using Grass-like Alumina and Fluoropolymer. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 49957-49962	9.5	18
324	Hybrid GaAs nanowire-polymer device on glass: Al-doped ZnO (AZO) as transparent conductive oxide for nanowire based photovoltaic applications. <i>Journal of Crystal Growth</i> , <b>2020</b> , 548, 125840	1.6	2

323	Review of fabrication methods of large-area transparent graphene electrodes for industry. <i>Frontiers of Optoelectronics</i> , <b>2020</b> , 13, 91-113	2.8	13
322	Nanowire Oligomer Waveguide Modes towards Reduced Lasing Threshold. <i>Materials</i> , <b>2020</b> , 13,	3.5	1
321	Growth of GaAs nanowire-graphite nanoplatelet hybrid structures. <i>CrystEngComm</i> , <b>2019</b> , 21, 6165-6172	3.3	3
320	Enhanced Tunneling in a Hybrid of Single-Walled Carbon Nanotubes and Graphene. <i>ACS Nano</i> , <b>2019</b> , 13, 11522-11529	16.7	13
319	Ultra-high on-chip optical gain in erbium-based hybrid slot waveguides. <i>Nature Communications</i> , <b>2019</b> , 10, 432	17.4	57
318	Aluminum Nitride Transition Layer for Power Electronics Applications Grown by Plasma-Enhanced Atomic Layer Deposition. <i>Materials</i> , <b>2019</b> , 12,	3.5	10
317	High photoresponsivity and broadband photodetection with a band-engineered WSe/SnSe heterostructure. <i>Nanoscale</i> , <b>2019</b> , 11, 3240-3247	7.7	49
316	Single-photon sources with quantum dots in III-V nanowires. <i>Nanophotonics</i> , <b>2019</b> , 8, 747-769	6.3	23
315	Determination of Young's Modulus of Wurtzite III-V Nanowires by the Methods of Scanning Probe Microscopy. <i>Journal of Surface Investigation</i> , <b>2019</b> , 13, 53-55	0.5	
314	Site-specific growth of oriented ZnO nanocrystal arrays. <i>Beilstein Journal of Nanotechnology</i> , <b>2019</b> , 10, 274-280	3	1
313	InAs-Nanowire-Based Broadband Ultrafast Optical Switch. <i>Journal of Physical Chemistry Letters</i> , <b>2019</b> , 10, 4429-4436	6.4	10
312	. <i>Chinese Optics Letters</i> , <b>2019</b> , 17, 062301	2.2	2
311	Surface potential response from GaP nanowires synthesized with mixed crystal phases. <i>Journal of Physics: Conference Series</i> , <b>2019</b> , 1400, 044018	0.3	1
310	Low-Temperature Plasma-Enhanced Atomic Layer Deposition of SiO Using Carbon Dioxide. <i>Nanoscale Research Letters</i> , <b>2019</b> , 14, 55	5	2
309	Thermal conductivity suppression in GaAs-AlAs core-shell nanowire arrays. <i>Nanoscale</i> , <b>2019</b> , 11, 20507-20513	7.5	7
308	Ultrafast Dynamics of Photoinduced Electron-Hole Plasma in Semiconductor Nanowires. <i>Semiconductors</i> , <b>2018</b> , 52, 19-23	0.7	
307	III-V nanowires on black silicon and low-temperature growth of self-catalyzed rectangular InAs NWs. <i>Scientific Reports</i> , <b>2018</b> , 8, 6410	4.9	9
306	Effect of Surface Wear on Corrosion Protection of Steel by CrN Coatings Sealed with Atomic Layer Deposition. <i>ACS Omega</i> , <b>2018</b> , 3, 1791-1800	3.9	11

305	Atomic layer deposition of AlN from AlCl <sub>3</sub> using NH <sub>3</sub> and Ar/NH <sub>3</sub> plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2018</b> , 36, 021508	2.9	15
304	Tribological properties of thin films made by atomic layer deposition sliding against silicon. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2018</b> , 36, 01A122	2.9	7
303	Lifetimes of the Vibrational States of DNA Molecules in Functionalized Complexes of Semiconductor Quantum Dots. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 70-72	0.7	3
302	Nonlinear Optics with 2D Layered Materials. <i>Advanced Materials</i> , <b>2018</b> , 30, e1705963	24	309
301	Transfer and patterning of chemical vapor deposited graphene by a multifunctional polymer film. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 073107	3.4	6
300	Active synchronization and modulation of fiber lasers with a graphene electro-optic modulator. <i>Optics Letters</i> , <b>2018</b> , 43, 3497-3500	3	10
299	Nanowire network-based multifunctional all-optical logic gates. <i>Science Advances</i> , <b>2018</b> , 4, eaar7954	14.3	30
298	Identifying threading dislocation types in ammonothermally grown bulk GaN by confocal Raman 3-D imaging of volumetric stress distribution. <i>Journal of Crystal Growth</i> , <b>2018</b> , 499, 47-54	1.6	11
297	Photoresponse of Graphene-Gated Graphene-GaSe Heterojunction Devices. <i>ACS Applied Nano Materials</i> , <b>2018</b> , 1, 3895-3902	5.6	13
296	Comparison of mechanical properties and composition of magnetron sputter and plasma enhanced atomic layer deposition aluminum nitride films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2018</b> , 36, 051508	2.9	7
295	Low-Power Continuous-Wave Second Harmonic Generation in Semiconductor Nanowires. <i>Laser and Photonics Reviews</i> , <b>2018</b> , 12, 1800126	8.3	4
294	Nonlinear Optics: Nonlinear Optics with 2D Layered Materials (Adv. Mater. 24/2018). <i>Advanced Materials</i> , <b>2018</b> , 30, 1870172	24	3
293	Demonstration of longitudinally polarized optical needles. <i>Optics Express</i> , <b>2018</b> , 26, 27572-27584	3.3	17
292	New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. <i>Nanotechnology</i> , <b>2018</b> , 29, 045602	3.4	5
291	Optical Properties of Bulk Gallium Oxide Grown from the Melt. <i>Reviews on Advanced Materials Science</i> , <b>2018</b> , 57, 97-103	4.8	3
290	A MoSe <sub>2</sub> /WSe <sub>2</sub> Heterojunction-Based Photodetector at Telecommunication Wavelengths. <i>Advanced Functional Materials</i> , <b>2018</b> , 28, 1804388	15.6	60
289	Influence of plasma parameters on the properties of ultrathin Al <sub>2</sub> O <sub>3</sub> films prepared by plasma enhanced atomic layer deposition below 100 °C for moisture barrier applications. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 125502	1.4	8
288	Optical harmonic generation in monolayer group-VI transition metal dichalcogenides. <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	53

287	Wide-band 'black silicon' with atomic layer deposited NbN. <i>Nanotechnology</i> , <b>2018</b> , 29, 335303	3.4	2
286	Corrosion protection of steel with multilayer coatings: Improving the sealing properties of physical vapor deposition CrN coatings with Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> atomic layer deposition nanolaminates. <i>Thin Solid Films</i> , <b>2017</b> , 627, 59-68	2.2	22
285	Rapid and Large-Area Characterization of Exfoliated Black Phosphorus Using Third-Harmonic Generation Microscopy. <i>Journal of Physical Chemistry Letters</i> , <b>2017</b> , 8, 1343-1350	6.4	50
284	Graphene actively Q-switched lasers. <i>2D Materials</i> , <b>2017</b> , 4, 025095	5.9	29
283	Crystal quality of two-dimensional gallium telluride and gallium selenide using Raman fingerprint. <i>AIP Advances</i> , <b>2017</b> , 7, 015014	1.5	29
282	Tailorable second-harmonic generation from an individual nanowire using spatially phase-shaped beams. <i>Laser and Photonics Reviews</i> , <b>2017</b> , 11, 1600175	8.3	19
281	Direct transfer of wafer-scale graphene films. <i>2D Materials</i> , <b>2017</b> , 4, 035004	5.9	26
280	Young's Modulus of Wurtzite and Zinc Blende InP Nanowires. <i>Nano Letters</i> , <b>2017</b> , 17, 3441-3446	11.5	22
279	New Approach for Thickness Determination of Solution-Deposited Graphene Thin Films. <i>ACS Omega</i> , <b>2017</b> , 2, 2630-2638	3.9	7
278	Nanowire encapsulation with polymer for electrical isolation and enhanced optical properties. <i>Nano Research</i> , <b>2017</b> , 10, 2657-2666	10	9
277	Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2017</b> , 35, 01B105	2.9	28
276	Review Article: Recommended reading list of early publications on atomic layer deposition Outcome of the Virtual Project on the History of ALD <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2017</b> , 35, 010801	2.9	55
275	I <sub>V</sub> curve hysteresis induced by gate-free charging of GaAs nanowires' surface oxide. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 132104	3.4	7
274	Ultra-strong nonlinear optical processes and trigonal warping in MoS layers. <i>Nature Communications</i> , <b>2017</b> , 8, 893	17.4	123
273	Versatile Water-Based Transfer of Large-Area Graphene Films onto Flexible Substrates. <i>MRS Advances</i> , <b>2017</b> , 2, 3749-3754	0.7	1
272	Probing the longitudinal electric field of Bessel beams using second-harmonic generation from nano-objects. <i>Journal of Optics (United Kingdom)</i> , <b>2017</b> , 19, 084011	1.7	3
271	MBE growth of nanowires using colloidal Ag nanoparticles. <i>Journal of Physics: Conference Series</i> , <b>2017</b> , 864, 012010	0.3	2
270	Scaling of graphene field-effect transistors supported on hexagonal boron nitride: radio-frequency stability as a limiting factor. <i>Nanotechnology</i> , <b>2017</b> , 28, 485203	3.4	10

269	Optically excited THz generation from ordered arrays of GaAs nanowires. <i>Procedia Engineering</i> , <b>2017</b> , 201, 100-104		1
268	Spontaneous and stimulated emission in InAsSb-based LED heterostructures. <i>Infrared Physics and Technology</i> , <b>2017</b> , 85, 246-250	2.7	12
267	Electroluminescence of InAs/InAs(Sb)/InAsSbP LED heterostructures in the temperature range 4.2-300 K. <i>Semiconductors</i> , <b>2017</b> , 51, 239-244	0.7	5
266	Rapid visualization of grain boundaries in monolayer MoS by multiphoton microscopy. <i>Nature Communications</i> , <b>2017</b> , 8, 15714	17.4	93
265	Measurement of Nanowire Optical Modes Using Cross-Polarization Microscopy. <i>Scientific Reports</i> , <b>2017</b> , 7, 17790	4.9	6
264	Nonlinear imaging of nanostructures using beams with binary phase modulation. <i>Optics Express</i> , <b>2017</b> , 25, 10441-10448	3.3	3
263	Nonlinear microscopy using cylindrical vector beams: Applications to three-dimensional imaging of nanostructures. <i>Optics Express</i> , <b>2017</b> , 25, 12463-12468	3.3	20
262	Lithography-free shell-substrate isolation for core-shell GaAs nanowires. <i>Nanotechnology</i> , <b>2016</b> , 27, 275603	3.4	1
261	Synthesis and properties of ultra-long InP nanowires on glass. <i>Nanotechnology</i> , <b>2016</b> , 27, 505606	3.4	5
260	Direct observation of confined acoustic phonon polarization branches in free-standing semiconductor nanowires. <i>Nature Communications</i> , <b>2016</b> , 7, 13400	17.4	51
259	Pyrolytic carbon coated black silicon. <i>Scientific Reports</i> , <b>2016</b> , 6, 25922	4.9	9
258	Synchrotron X-ray diffraction topography study of bonding-induced strain in silicon-on-insulator wafers. <i>Thin Solid Films</i> , <b>2016</b> , 603, 435-440	2.2	1
257	A technique for large-area position-controlled growth of GaAs nanowire arrays. <i>Nanotechnology</i> , <b>2016</b> , 27, 135601	3.4	9
256	Direct comparison of second and third harmonic generation in mono- and few-layer MX <sub>2</sub> (M=Mo,W; X=S,Se) by multiphoton microscope <b>2016</b> ,		2
255	Influence of surface passivation on electric properties of individual GaAs nanowires studied by current-voltage AFM measurements. <i>Lithuanian Journal of Physics</i> , <b>2016</b> , 56,	1.1	10
254	Growth and properties of self-catalyzed (In,Mn)As nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2016</b> , 10, 554-557	2.5	3
253	Tunable Graphene-GaSe Dual Heterojunction Device. <i>Advanced Materials</i> , <b>2016</b> , 28, 1845-52	24	76
252	Direct measurement of elastic modulus of InP nanowires with Scanning Probe Microscopy in PeakForce QNM mode. <i>Journal of Physics: Conference Series</i> , <b>2016</b> , 769, 012029	0.3	3

251	Protective capping and surface passivation of III-V nanowires by atomic layer deposition. <i>AIP Advances</i> , <b>2016</b> , 6, 015016	1.5	18
250	Surface passivation of GaAs nanowires by the atomic layer deposition of AlN. <i>Semiconductors</i> , <b>2016</b> , 50, 1619-1621	0.7	0
249	Structural and chemical analysis of annealed plasma-enhanced atomic layer deposition aluminum nitride films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2016</b> , 34, 041506	2.9	20
248	Second and third harmonic generation in few-layer gallium telluride characterized by multiphoton microscopy. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 073103	3.4	41
247	Resonant features of the terahertz generation in semiconductor nanowires. <i>Semiconductors</i> , <b>2016</b> , 50, 1561-1565	0.7	2
246	Black phosphorus polycarbonate polymer composite for pulsed fibre lasers. <i>Applied Materials Today</i> , <b>2016</b> , 4, 17-23	6.6	74
245	Optical characterization of directly deposited graphene on a dielectric substrate. <i>Optics Express</i> , <b>2016</b> , 24, 2965-70	3.3	5
244	TEM study of defect structure of GaN epitaxial films grown on GaN/Al <sub>2</sub> O <sub>3</sub> substrates with buried column pattern. <i>Journal of Crystal Growth</i> , <b>2016</b> , 445, 30-36	1.6	3
243	Thermal conductivity of amorphous Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> nanolaminates deposited by atomic layer deposition. <i>Nanotechnology</i> , <b>2016</b> , 27, 445704	3.4	16
242	Atomic Layer Engineering of Er-Ion Distribution in Highly Doped Er:Al <sub>2</sub> O <sub>3</sub> for Photoluminescence Enhancement. <i>ACS Photonics</i> , <b>2016</b> , 3, 2040-2048	6.3	19
241	Processing and characterization of epitaxial GaAs radiation detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2015</b> , 796, 51-55	1.2	8
240	Solubility of Boron, Carbon, and Nitrogen in Transition Metals: Getting Insight into Trends from First-Principles Calculations. <i>Journal of Physical Chemistry Letters</i> , <b>2015</b> , 6, 3263-3268	6.4	40
239	Optical limiting in solutions of InP and GaAs nanowires and hybrid systems based on such nanocrystals. <i>Technical Physics Letters</i> , <b>2015</b> , 41, 120-123	0.7	3
238	All-Graphene Three-Terminal-Junction Field-Effect Devices as Rectifiers and Inverters. <i>ACS Nano</i> , <b>2015</b> , 9, 5666-74	16.7	12
237	Slot waveguide ring resonators coated by an atomic layer deposited organic/inorganic nanolaminate. <i>Optics Express</i> , <b>2015</b> , 23, 26940-51	3.3	11
236	Nanotribological, nanomechanical and interfacial characterization of atomic layer deposited TiO <sub>2</sub> on a silicon substrate. <i>Wear</i> , <b>2015</b> , 342-343, 270-278	3.5	11
235	The effect of resonant Mie absorption under THz radiation emission in semiconductor nanowires. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , <b>2015</b> , 119, 754-758	0.7	1
234	Polarization and Thickness Dependent Absorption Properties of Black Phosphorus: New Saturable Absorber for Ultrafast Pulse Generation. <i>Scientific Reports</i> , <b>2015</b> , 5, 15899	4.9	225



233	Wafer-scale self-organized InP nanopillars with controlled orientation for photovoltaic devices. <i>Nanotechnology</i> , <b>2015</b> , 26, 415304	3.4	10
232	Generation of terahertz radiation in ordered arrays of GaAs nanowires. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 252104	3.4	15
231	Observation of linear I-V curves on vertical GaAs nanowires with atomic force microscope. <i>Journal of Physics: Conference Series</i> , <b>2015</b> , 661, 012031	0.3	3
230	Broadband laser polarization control with aligned carbon nanotubes. <i>Nanoscale</i> , <b>2015</b> , 7, 11199-205	7.7	11
229	A physics-based model of gate-tunable metal-graphene contact resistance benchmarked against experimental data. <i>2D Materials</i> , <b>2015</b> , 2, 025006	5.9	22
228	Investigation of second- and third-harmonic generation in few-layer gallium selenide by multiphoton microscopy. <i>Scientific Reports</i> , <b>2015</b> , 5, 10334	4.9	76
227	Second-harmonic generation imaging of semiconductor nanowires with focused vector beams. <i>Nano Letters</i> , <b>2015</b> , 15, 1564-9	11.5	53
226	Fabrication of dual-type nanowire arrays on a single substrate. <i>Nano Letters</i> , <b>2015</b> , 15, 1679-83	11.5	8
225	Improved SERS Intensity from Silver-Coated Black Silicon by Tuning Surface Plasmons. <i>Advanced Materials Interfaces</i> , <b>2014</b> , 1, 1300008	4.6	13
224	X-ray reflectivity characterization of atomic layer deposition Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> nanolaminates with ultrathin bilayers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2014</b> , 32, 01A111	2.9	24
223	Thermal and plasma enhanced atomic layer deposition of SiO <sub>2</sub> using commercial silicon precursors. <i>Thin Solid Films</i> , <b>2014</b> , 558, 93-98	2.2	50
222	Photo-induced electron transfer at nanostructured semiconductor-zinc porphyrin interface. <i>Chemical Physics Letters</i> , <b>2014</b> , 592, 47-51	2.5	11
221	Functionalization of nc-Si/SiO <sub>2</sub> semiconductor quantum dots by oligonucleotides. <i>Semiconductors</i> , <b>2014</b> , 48, 1485-1489	0.7	2
220	Electrical detection of picosecond acoustic pulses in vertical transport devices with nanowires. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 062102	3.4	2
219	Synchrotron radiation x-ray topography and defect selective etching analysis of threading dislocations in GaN. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 083504	2.5	33
218	Defect structure of a free standing GaN wafer grown by the ammonothermal method. <i>Journal of Crystal Growth</i> , <b>2014</b> , 406, 72-77	1.6	11
217	Large-area analysis of dislocations in ammonothermal GaN by synchrotron radiation X-ray topography. <i>Applied Physics Express</i> , <b>2014</b> , 7, 091003	2.4	20
216	Properties of atomic-layer-deposited ultra-thin AlN films on GaAs surfaces. <i>Applied Surface Science</i> , <b>2014</b> , 314, 570-574	6.7	3

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73	Evolution of Self-Assembled InAs/InP Islands into Quantum Rings. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L1323-L1325	1.4	3
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67	GaN/GaAs(1 0 0) superlattices grown by metalorganic vapor phase epitaxy using dimethylhydrazine precursor. <i>Journal of Crystal Growth</i> , <b>2004</b> , 270, 346-350	1.6	3
66	Self-assembled In(Ga) As islands on Ge substrate. <i>Journal of Crystal Growth</i> , <b>2004</b> , 272, 221-226	1.6	3
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64	The morphology of an InP wetting layer on GaAs. <i>Applied Surface Science</i> , <b>2004</b> , 229, 333-337	6.7	1
63	Optical waveguides on polysilicon-on-insulator. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2003</b> , 14, 417-420	2.1	4
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61	In(Ga)As quantum dots on Ge substrate. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2003</b> , 14, 349-352	2.1	4
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54	Longitudinal Stark Effect in Parabolic Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 2002-2005	6	

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48	Carrier capture processes in strain-induced $\text{In}_x\text{Ga}_{1-x}\text{As/GaAs}$ quantum dot structures. <i>Physical Review B</i> , <b>2000</b> , 62, 13588-13594	3-3	7
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44	Pauli-blocking imaging of single strain-induced semiconductor quantum dots. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3200-3202	3-4	29
43	Tailoring of Energy Levels in Strain-Induced Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 1081-1084	1.4	8
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29	Synchrotron X-ray topographic analysis of the impact of processing steps on the fabrication of AlGaAs/InGaAs p-HEMT's. <i>IEEE Transactions on Electron Devices</i> , <b>1996</b> , 43, 1085-1091	2.9	
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24	Zeeman Effect in Parabolic Quantum Dots. <i>Physical Review Letters</i> , <b>1996</b> , 77, 342-345	7.4	92
23	Optical spectroscopy of bragg confined transitions in a superlattice with multiquantum barriers. <i>Solid State Communications</i> , <b>1995</b> , 93, 525-528	1.6	3
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7	Study of GaAs/AlGaAs and InGaAs/InP quantum well structures using low-field transverse electroreflectance <b>1990</b> , 1286, 300		
6	Photoreflectance studies of InGaAs/InP superlattices <b>1990</b> , 1286, 238		
5	Room-temperature observation of impurity states in bulk GaAs by photoreflectance. <i>Journal of Applied Physics</i> , <b>1989</b> , 65, 2556-2557	2.5	23
4	Synchrotron section topographic study of defects in InP substrates and quaternary laser structures. <i>Journal of Crystal Growth</i> , <b>1989</b> , 96, 881-887	1.6	2
3	Photonic crystal slabs with ring-shaped holes in a triangular lattice		1
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